### NCE N-Channel Enhancement Mode Power MOSFET

### **Description**

The NCE4060K uses advanced trench technology and design to provide excellent  $R_{DS(ON)}$  with low gate charge. It can be used in a wide variety of applications.

#### **General Features**

V<sub>DS</sub> =40V,I<sub>D</sub> =60A

 $R_{DS(ON)}$  <8.5m $\Omega$  @  $V_{GS}$ =10V

 $R_{DS(ON)}$  <18m $\Omega$  @  $V_{GS}$ =4.5V

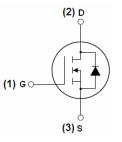
- High density cell design for ultra low Rdson
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high E<sub>AS</sub>
- Excellent package for good heat dissipation
- Special process technology for high ESD capability

### **Application**

- Load switching
- Hard switched and high frequency circuits
- Uninterruptible power supply

100% UIS TESTED!

100% ΔVds TESTED!



Schematic diagram



Marking and pin assignment



TO-252-2L top view

### **Package Marking and Ordering Information**

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCE4060K	NCE4060K	TO-252-2L	-	-	-

## Absolute Maximum Ratings (T<sub>C</sub>=25 ℃ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V <sub>DS</sub>	40	V
Gate-Source Voltage	V <sub>GS</sub>	±20	V
Drain Current-Continuous	I <sub>D</sub>	60	А
Drain Current-Continuous(T <sub>C</sub> =100°C)	I <sub>D</sub> (100°C)	42	Α
Pulsed Drain Current	I <sub>DM</sub>	200	А
Maximum Power Dissipation	P <sub>D</sub>	65	W
Derating factor		0.43	W/°C
Single pulse avalanche energy (Note 5)	E <sub>AS</sub>	400	mJ
Operating Junction and Storage Temperature Range	$T_{J}, T_{STG}$	-55 To 175	$^{\circ}$



## **Thermal Characteristic**

Thermal Resistance, Junction-to-Case <sup>(Note 2)</sup>	$R_{ heta JC}$	2.3	°C/W	
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## Electrical Characteristics (T<sub>C</sub>=25 °C unless otherwise noted)

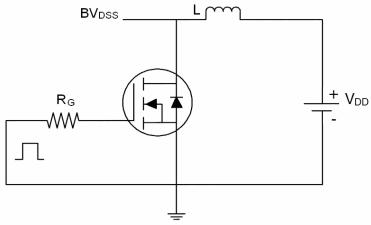
Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics	<u>.</u>			•		
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =250μA	40	45	-	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =40V,V <sub>GS</sub> =0V	-	-	1	μΑ
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V,V <sub>DS</sub> =0V	-	-	±100	nA
On Characteristics (Note 3)	·			•		
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS}=V_{GS},I_{D}=250\mu A$	1.2	1.6	2.0	V
Drain Source On State Registeres	В	V <sub>GS</sub> =10V, I <sub>D</sub> =20A	-	7.3	8.5	
Orain-Source On-State Resistance R <sub>DS(ON)</sub>		V <sub>GS</sub> =4.5V, I <sub>D</sub> =20A		15	18	mΩ
Forward Transconductance	<b>g</b> FS	V <sub>DS</sub> =10V,I <sub>D</sub> =20A	15	-	-	S
Dynamic Characteristics (Note4)	·			•		
Input Capacitance	C <sub>lss</sub>	\/ 00\/\/ 0\/	-	1800	-	PF
Output Capacitance	C <sub>oss</sub>	$V_{DS}$ =20V, $V_{GS}$ =0V, F=1.0MHz	-	280	-	PF
Reverse Transfer Capacitance	C <sub>rss</sub>	F=1.UIVIHZ	-	190	-	PF
Switching Characteristics (Note 4)	<u>.</u>			•		
Turn-on Delay Time	t <sub>d(on)</sub>		-	6.4	-	nS
Turn-on Rise Time	t <sub>r</sub>	$V_{DD}$ =20V, $I_D$ =2A, $R_L$ =1 $\Omega$	-	17.2	-	nS
Turn-Off Delay Time	$t_{d(off)}$	$V_{GS}$ =10 $V$ , $R_{G}$ =3 $\Omega$	-	29.6	-	nS
Turn-Off Fall Time	t <sub>f</sub>		-	16.8	-	nS
Total Gate Charge	Qg	V -20V I -20A	-	29		nC
Gate-Source Charge	Q <sub>gs</sub>	$V_{DS}$ =20V, $I_D$ =20A, $V_{GS}$ =10V	-	4.5		nC
Gate-Drain Charge	$Q_{gd}$	V <sub>GS</sub> =10V	-	6.4		nC
Drain-Source Diode Characteristics	<u>.</u>			•		
Diode Forward Voltage (Note 3)	$V_{SD}$	V <sub>GS</sub> =0V,I <sub>S</sub> =10A	-		1.2	V
Diode Forward Current (Note 2)	Is		-	-	60	Α
Reverse Recovery Time	t <sub>rr</sub>	TJ = 25°C, IF = 20A	-	29	-	nS
Reverse Recovery Charge	Qrr	$di/dt = 100A/\mu s^{(Note3)}$	-	26	-	nC
Forward Turn-On Time	t <sub>on</sub>	Intrinsic turn-on time is negligible (turn-on is dominated by LS+L				y LS+LD)

#### Notes

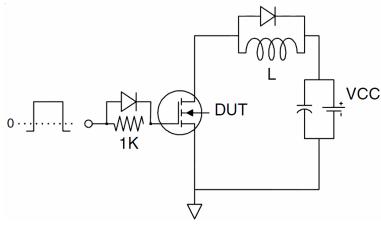
- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. Surface Mounted on FR4 Board, t ≤ 10 sec.
- 3. Pulse Test: Pulse Width  $\leq$  300 $\mu$ s, Duty Cycle  $\leq$  2%.
- **4.** Guaranteed by design, not subject to production
- **5.**  $E_{AS}$  condition : Tj=25  $^{\circ}\text{C}$  ,V\_DD=20V,V\_G=10V,L=1mH,Rg=25 $\Omega$  ,

## **Test circuit**

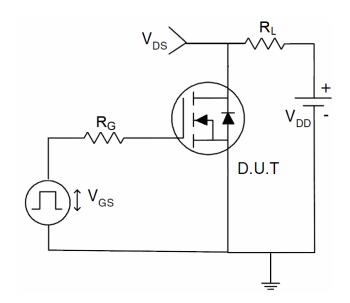
## 1) E<sub>AS</sub> Test Circuit



## 2) Gate Charge Test Circuit

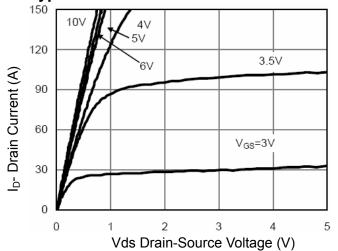


## 3) Switch Time Test Circuit

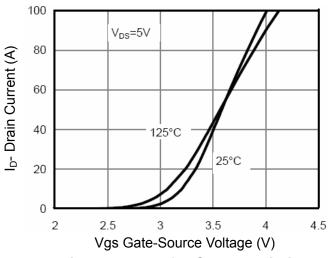




## **Typical Electrical and Thermal Characteristics (Curves)**



**Figure 1 Output Characteristics** 



**Figure 2 Transfer Characteristics** 

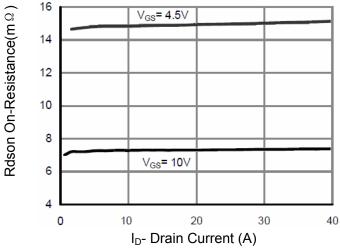


Figure 3 Rdson- Drain Current

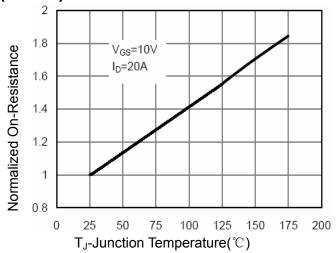


Figure 4 Rdson-JunctionTemperature

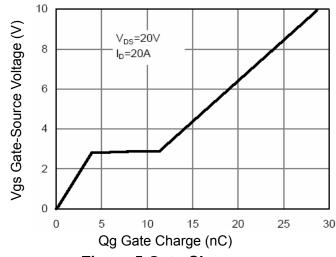


Figure 5 Gate Charge

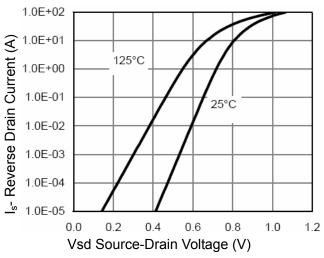
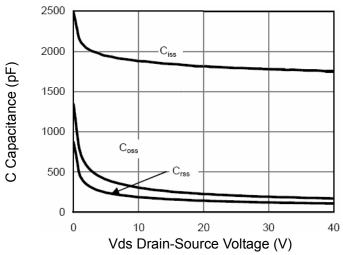


Figure 6 Source- Drain Diode Forward



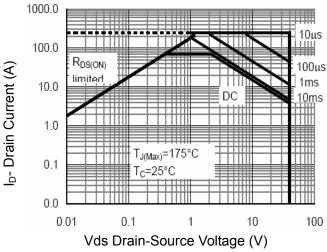


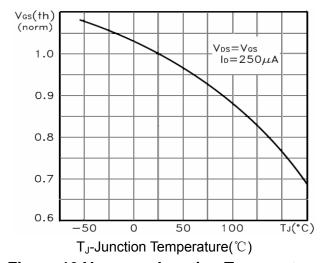
70

60

Figure 7 Capacitance vs Vds

 $T_J$ -Junction Temperature (°C) Figure 9 Power De-rating





**Figure 8 Safe Operation Area** 

Figure 10 V<sub>GS(th)</sub> vs Junction Temperature

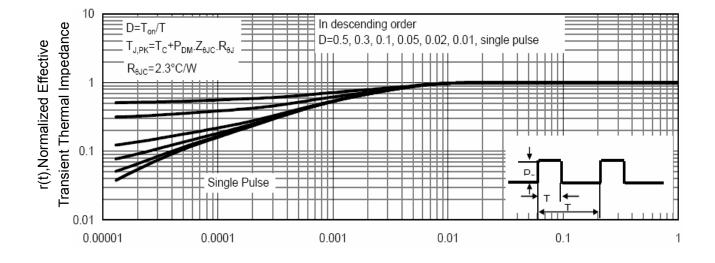
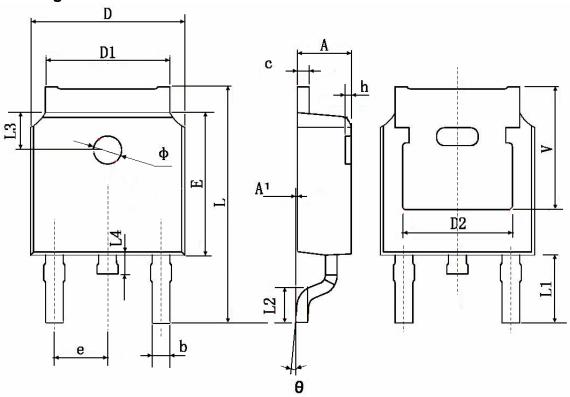


Figure 11 Normalized Maximum Transient Thermal Impedance

Square Wave Pluse Duration(sec)

# **TO-252 Package Information**



Symbol	Dimensions I	n Millimeters	Dimensions In Inches			
Symbol	Min.	Max.	Min.	Max.		
А	2.200	2.400	0.087	0.094		
A1	0.000	0.127	0.000	0.005		
b	0.660	0.860	0.026	0.034		
С	0.460	0.580	0.018	0.023		
D	6.500	6.700	0.256	0.264		
D1	5.100	5.460	0.201	0.215		
D2	4.830	4.830 TYP.		0.190 TYP.		
Е	6.000	6.200	0.236	0.244		
е	2.186	2.386	0.086	0.094		
L	9.800	10.400	0.386	0.409		
L1	2.900	TYP.	0.114 TYP.			
L2	1.400	1.700	0.055	0.067		
L3	1.600	TYP.	0.063	0.063 TYP.		
L4	0.600	1.000	0.024	0.039		
Ф	1.100	1.300	0.043	0.051		
θ	0°	8°	0°	8°		
h	0.000	0.300	0.000	0.012		
V	5.350	TYP.	0.211 TYP.			

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